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FIG. 1A
(PRIOR ART)

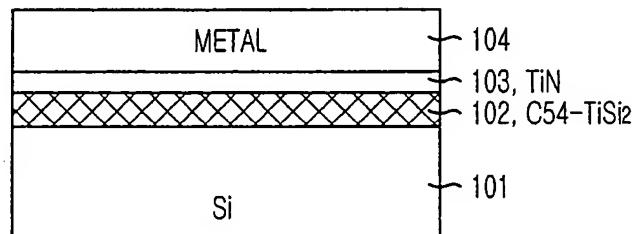


FIG. 1B
(PRIOR ART)

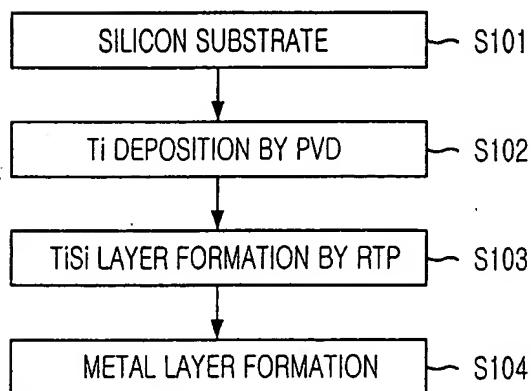


FIG. 2A

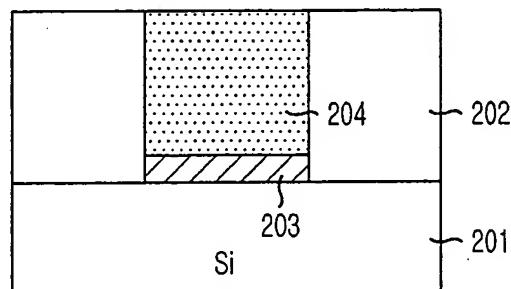


FIG. 2B

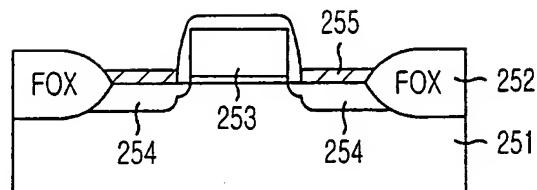


FIG. 3A

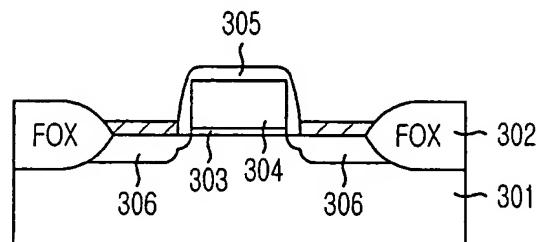


FIG. 3B

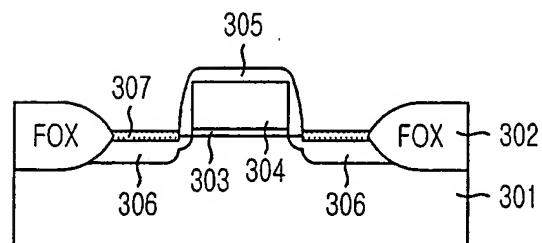


FIG. 3C

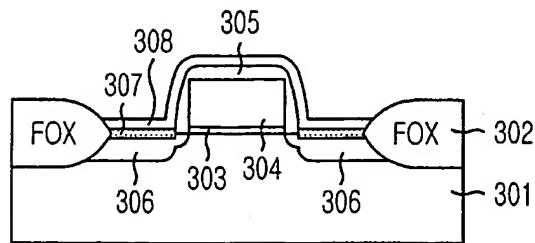
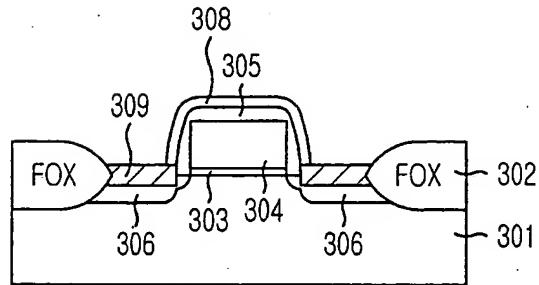
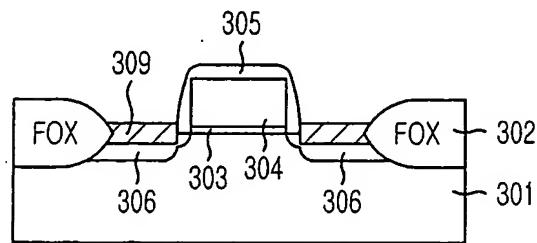


FIG. 3D



Blakely, Sokoloff, Taylor & Zafman LLP (310) 207-3800
Title: SEMICONDUCTOR DEVICE WITH EPITAXIAL C49-TITANIUM SILICIDE ($TiSi_2$) LAYER
AND METHOD FOR FABRICATING THE SAME
1st Named Inventor: Moon-Keun LEE
Express Mail No.: EV339912925US Docket No.: 51876P521
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FIG. 3E



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FIG. 4A

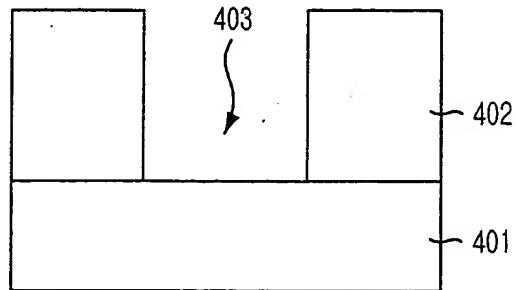


FIG. 4B

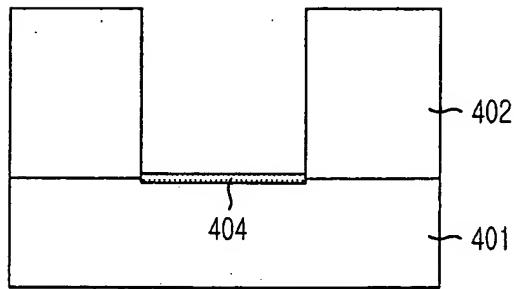


FIG. 4C

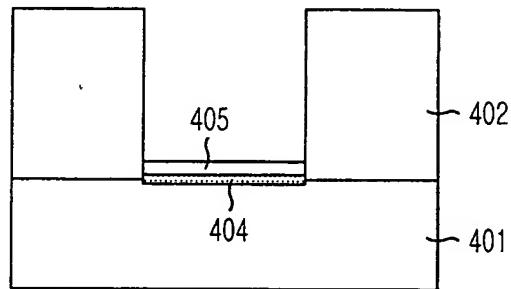


FIG. 4D

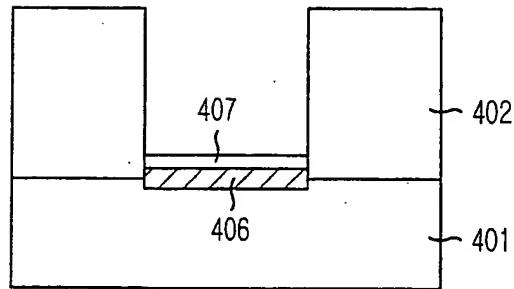


FIG. 4E

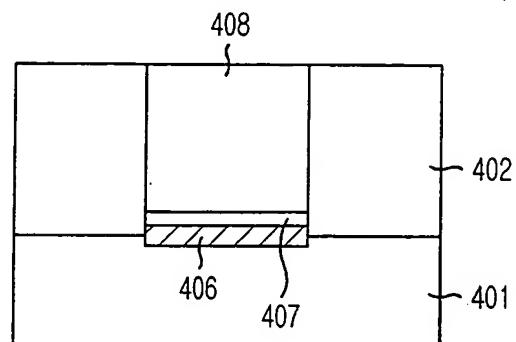


FIG. 5

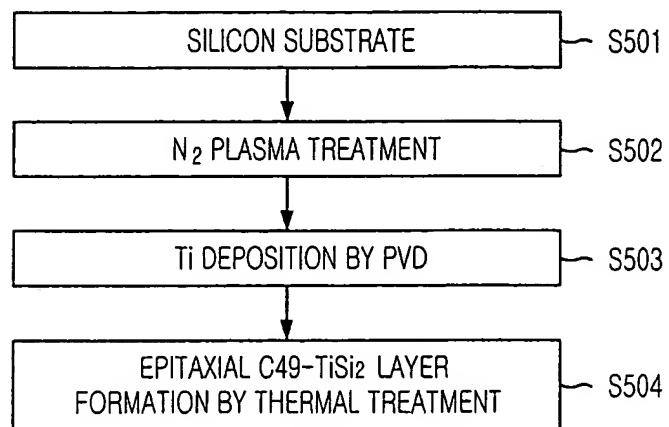
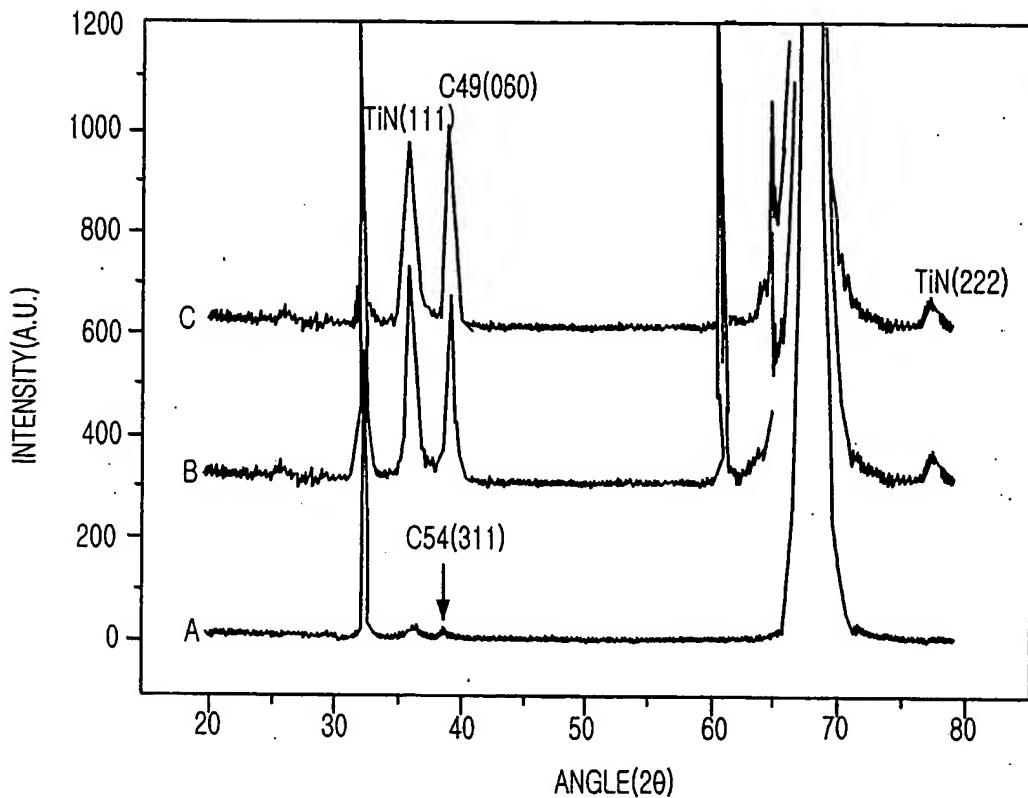


FIG. 6



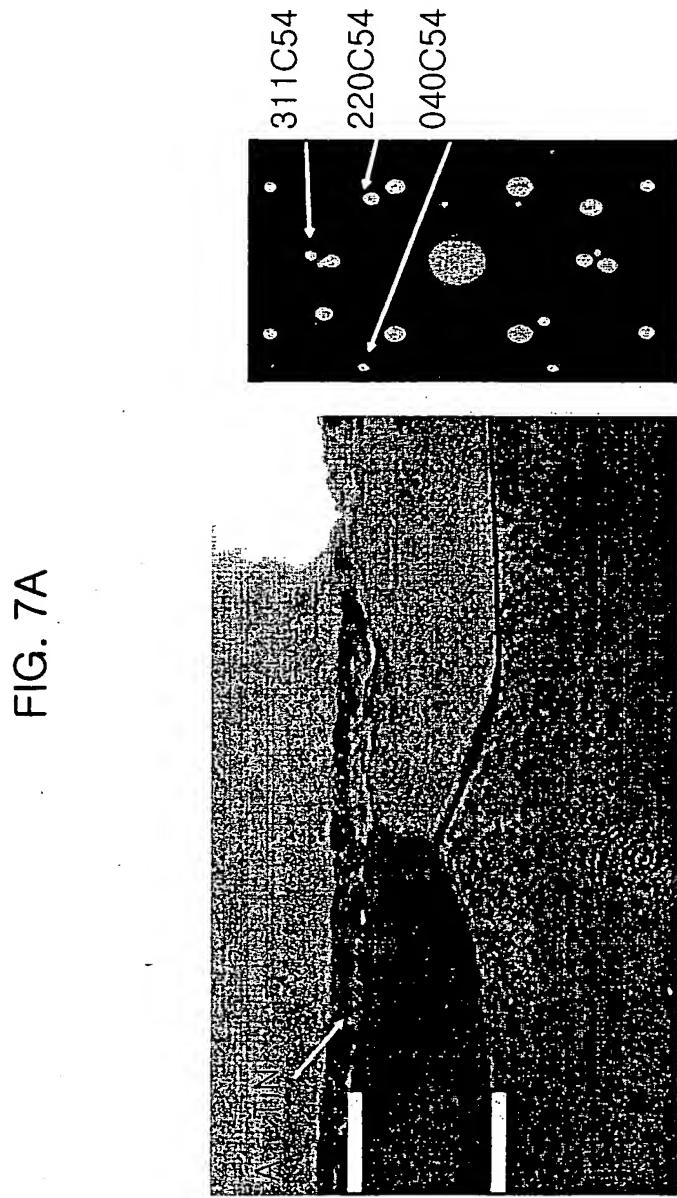


FIG. 7B

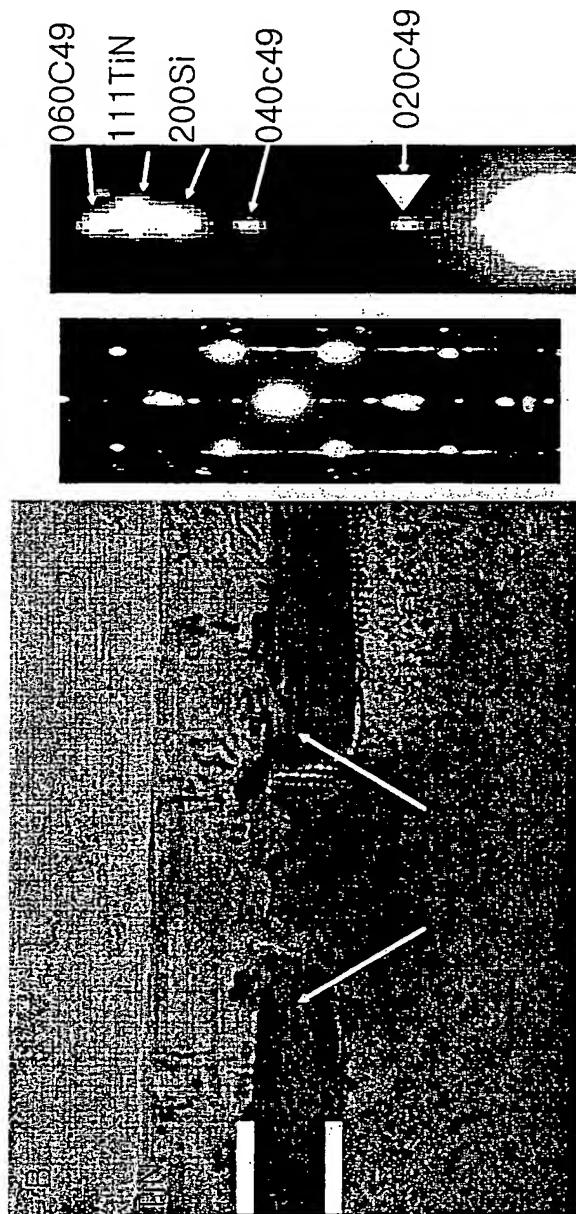


FIG. 8A

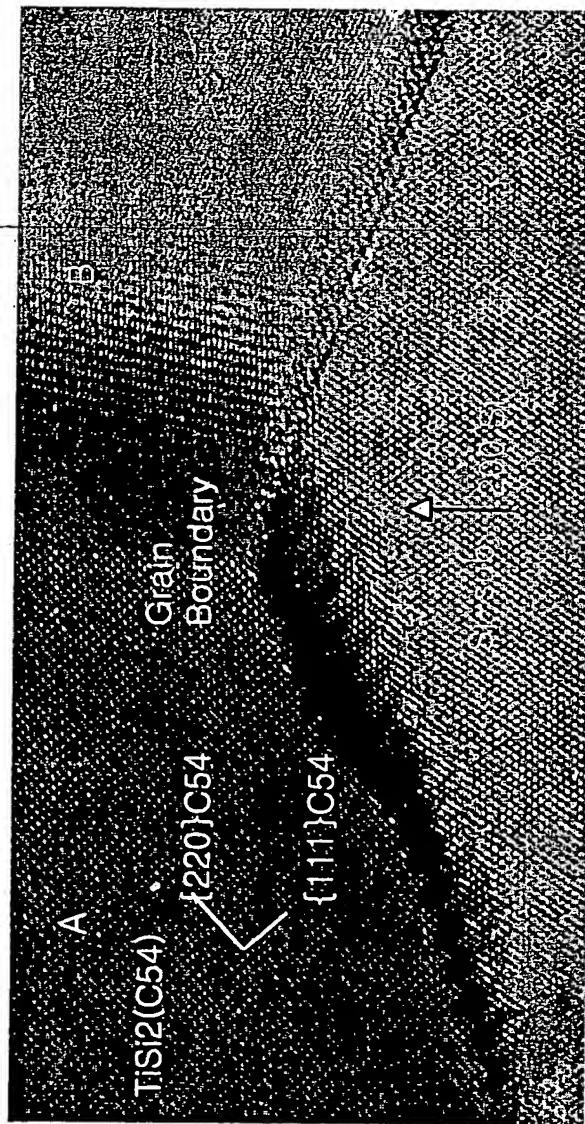


FIG. 8B

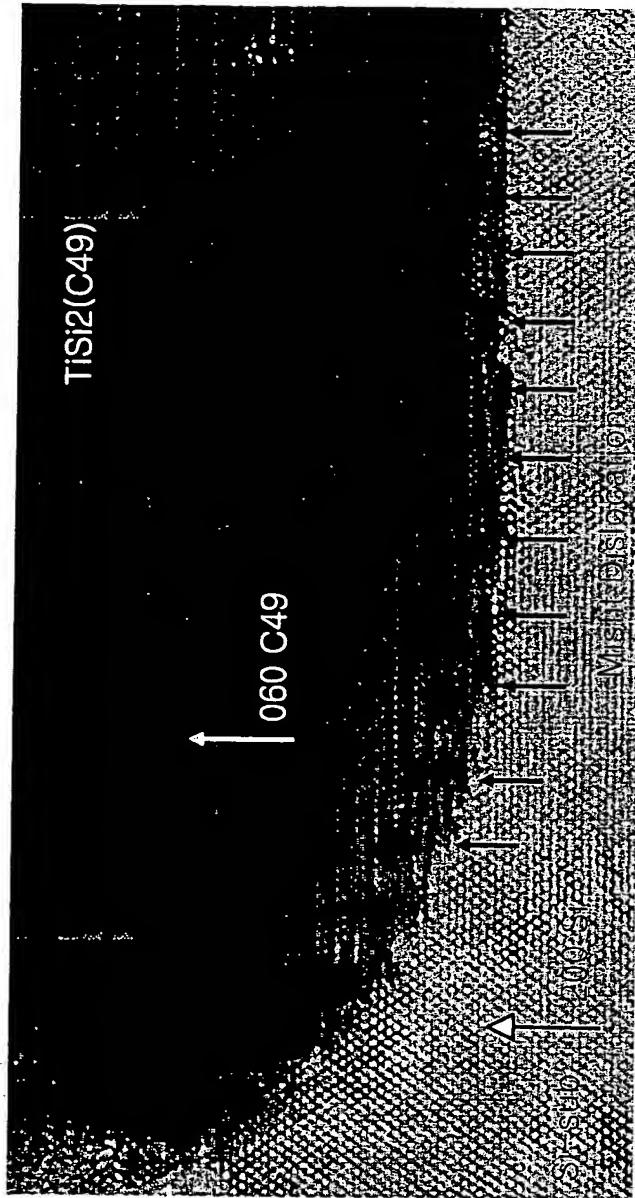


FIG. 9

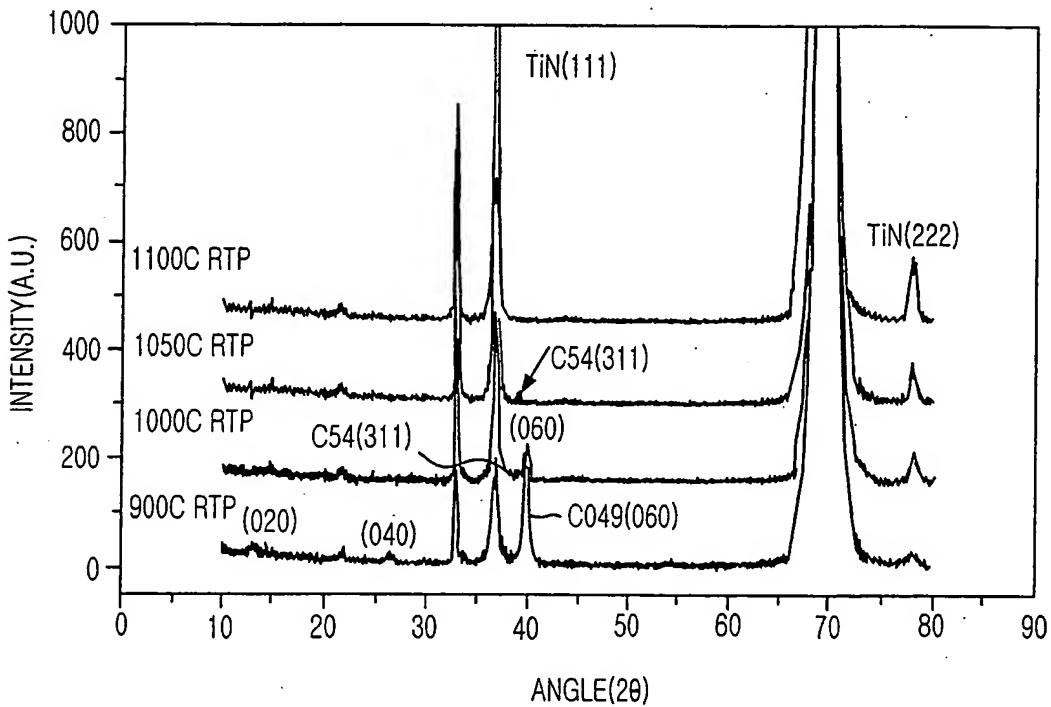
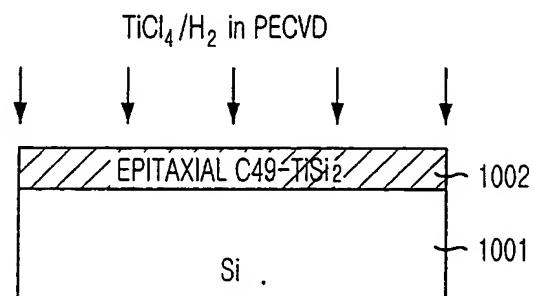


FIG. 10



Title: SEMICONDUCTOR DEVICE WITH EPITAXIAL C49-TITANIUM SILICIDE (TiSi₂) LAYER AND

METHOD FOR FABRICATING THE SAME

1st Named Inventor: Moon-Keun LEE

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FIG. 11A

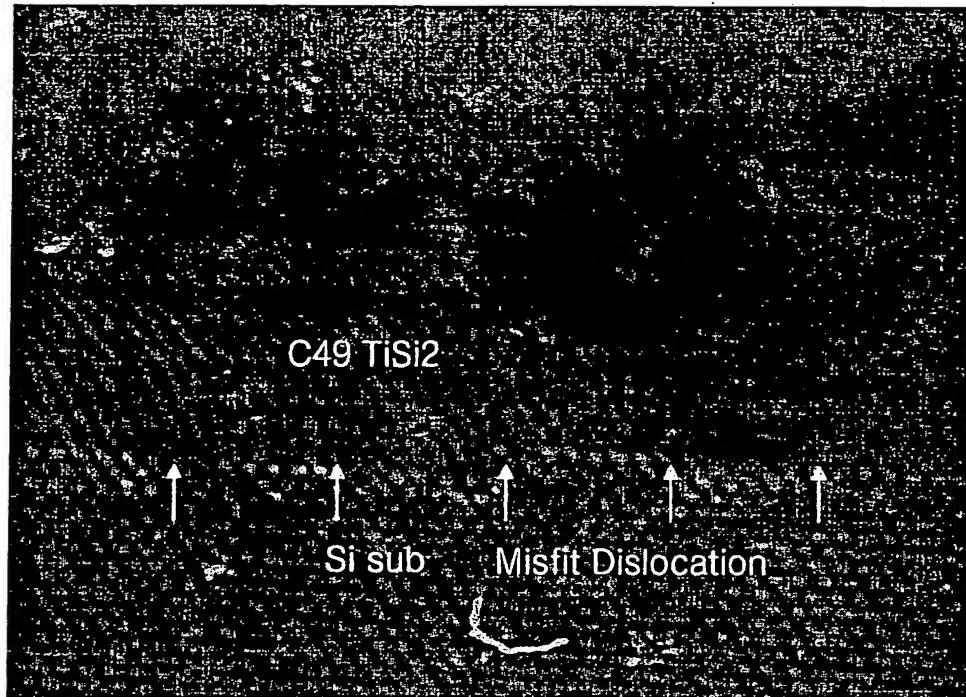


FIG. 11B

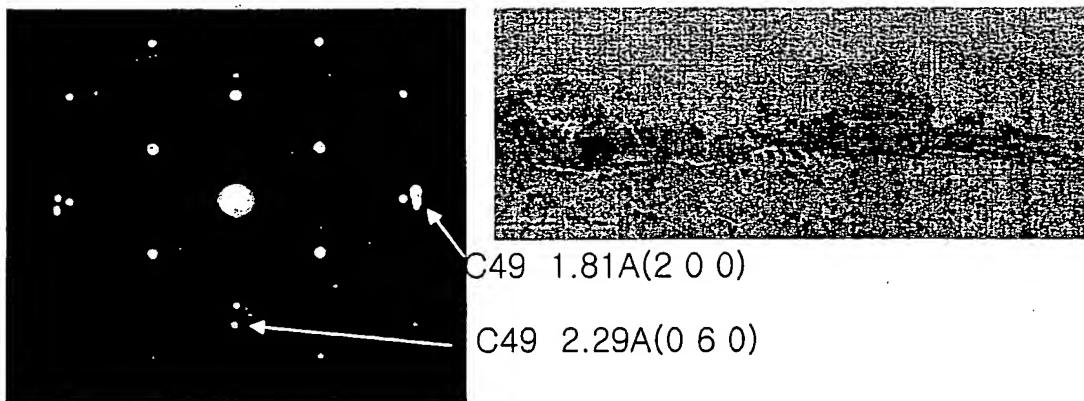


FIG. 12

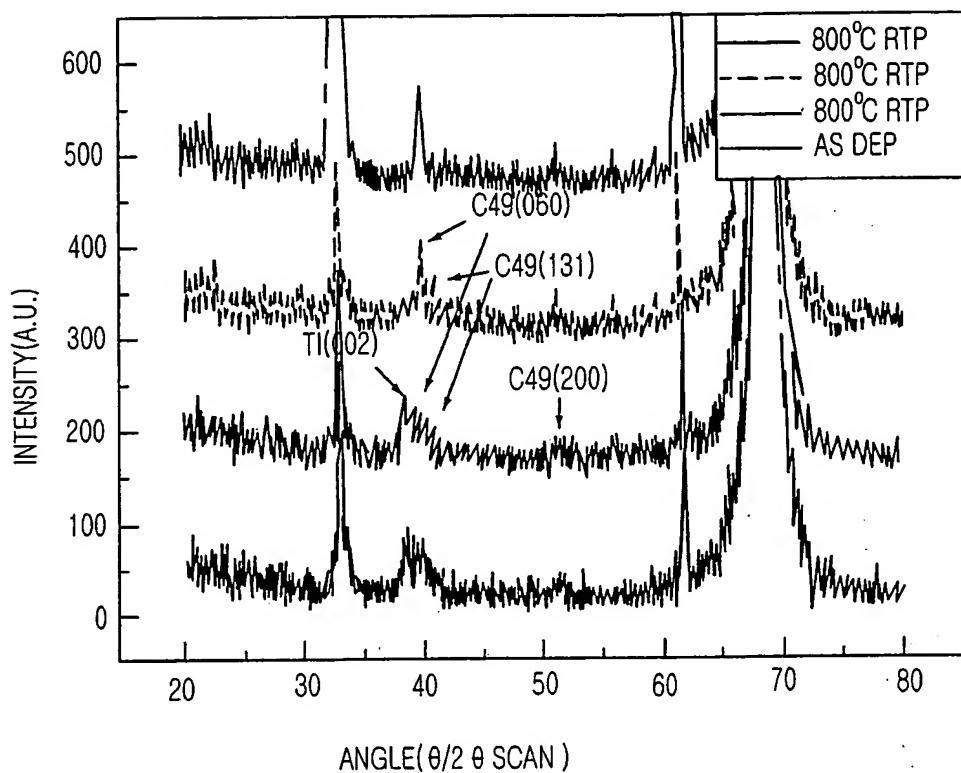


FIG. 13A



FIG. 13B

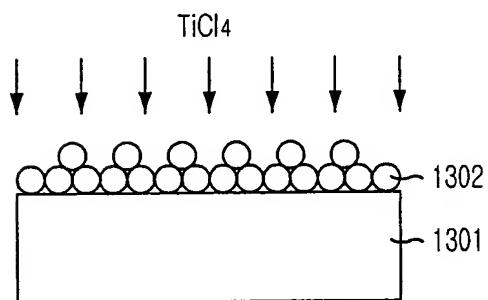
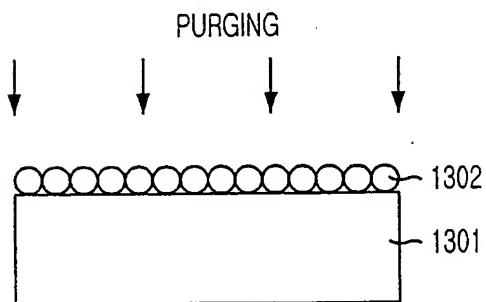


FIG. 13C



Title: SEMICONDUCTOR DEVICE WITH EPITAXIAL C49-TITANIUM SILICIDE (TiSi₂) LAYER

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1st Named Inventor: Moon-Keun LEE

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FIG. 13D

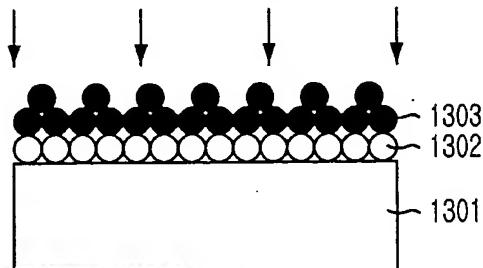
H₂ REDUCTION GAS

FIG. 13E

PURGING

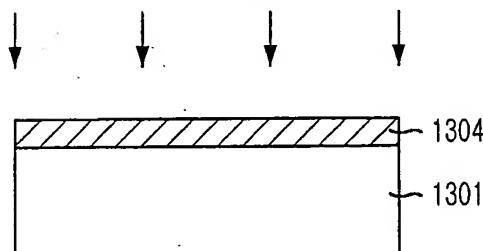


FIG. 13F

